

FIG. 1

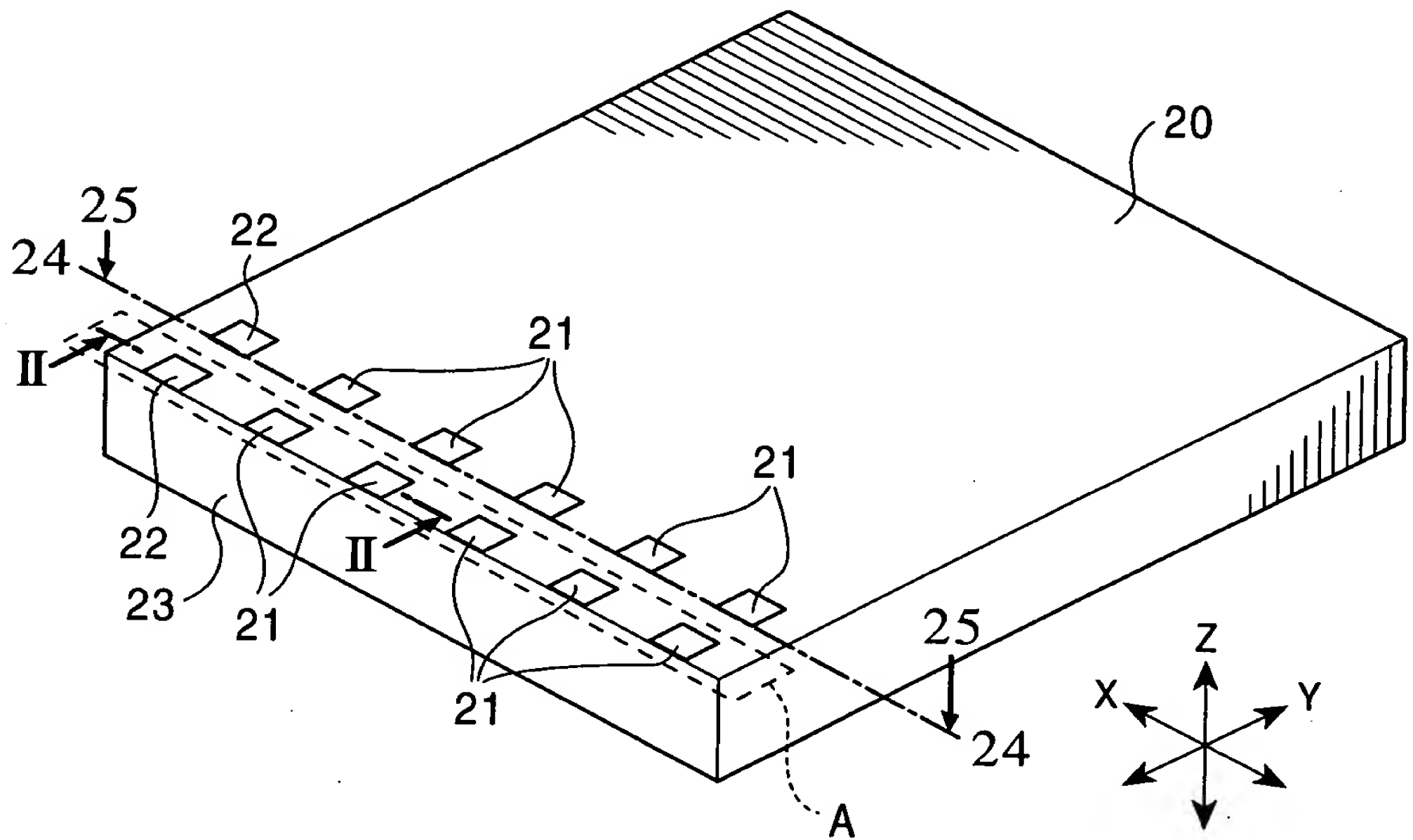


FIG. 2

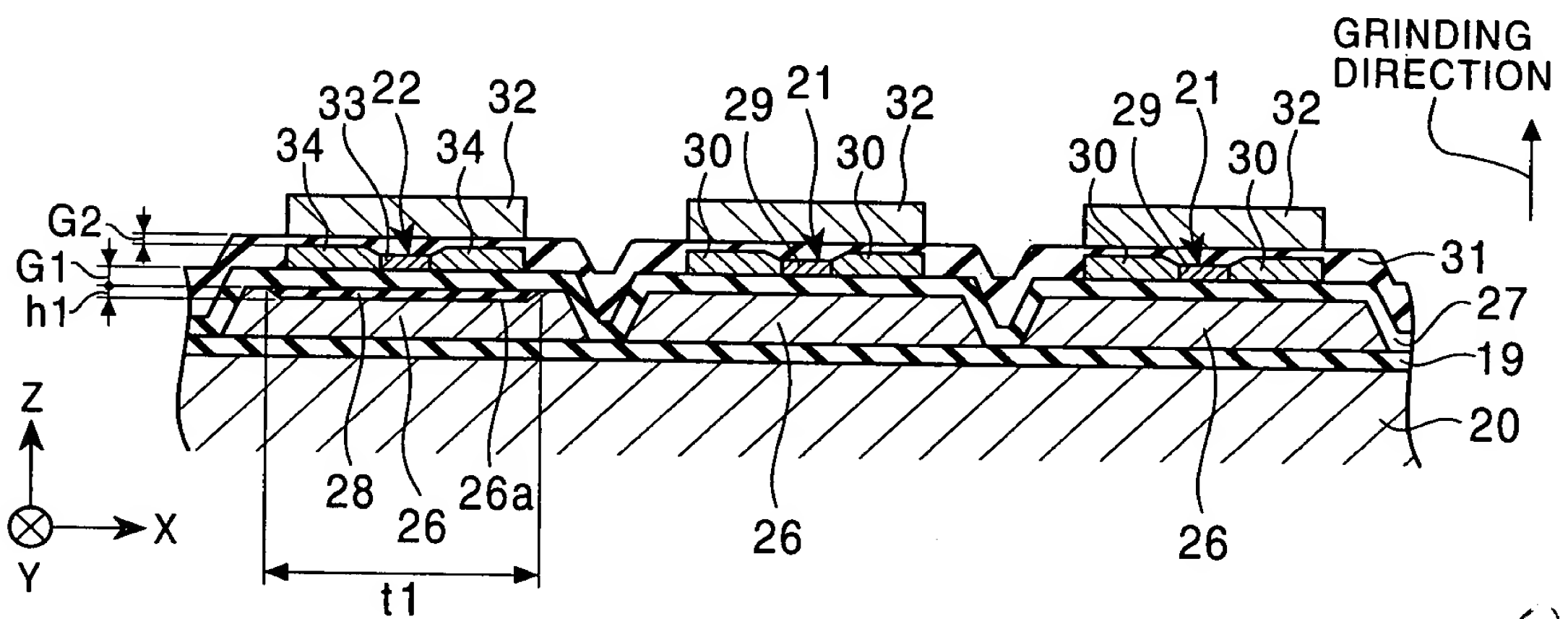


FIG. 3

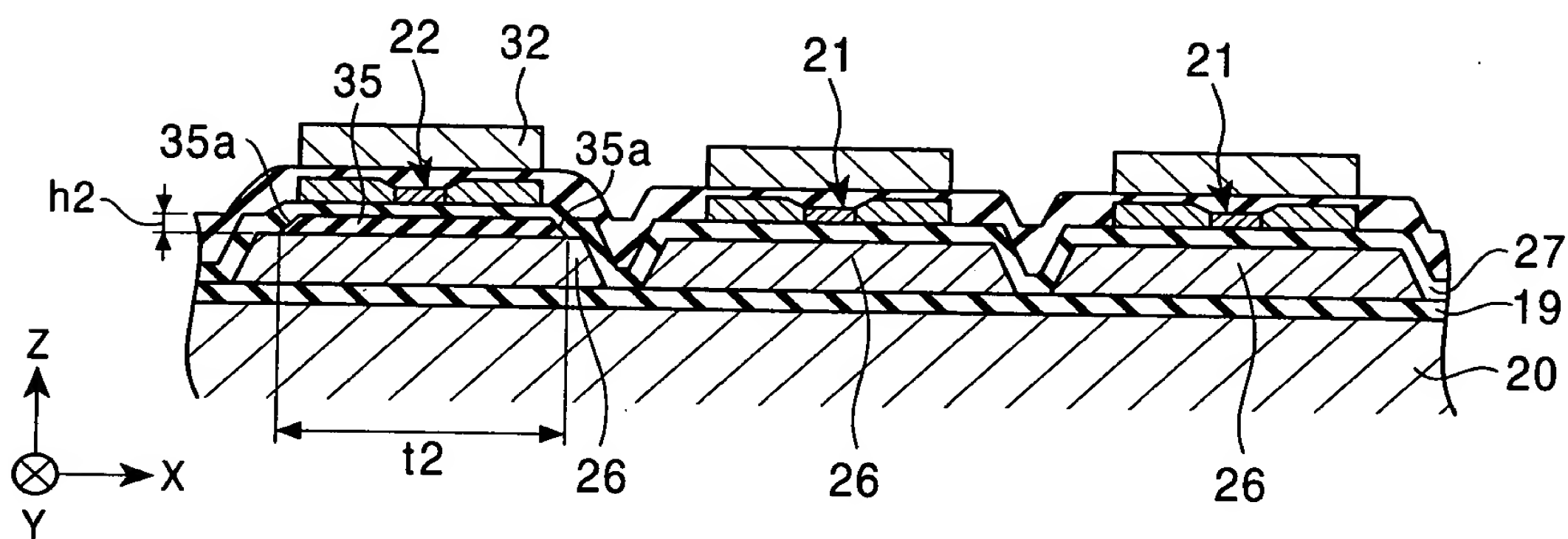
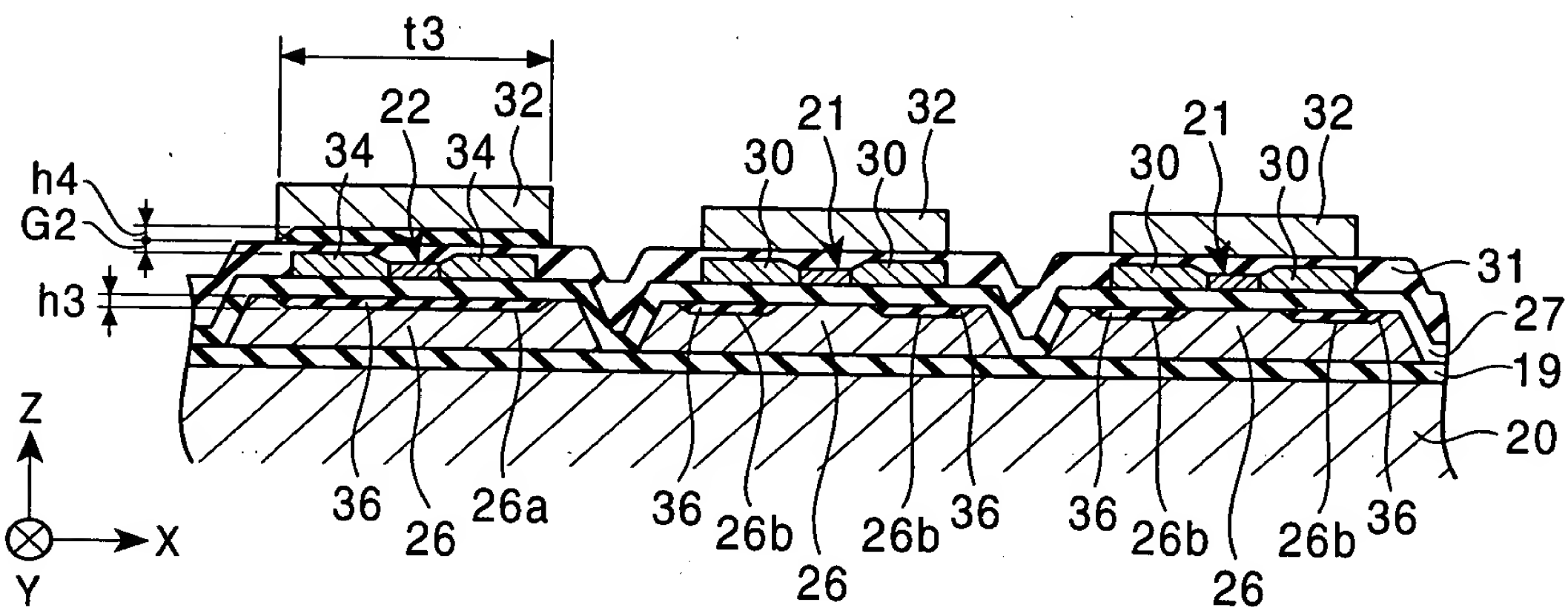


FIG. 4



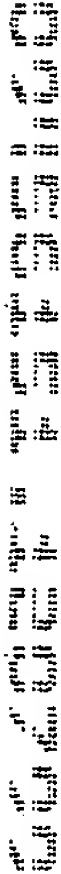
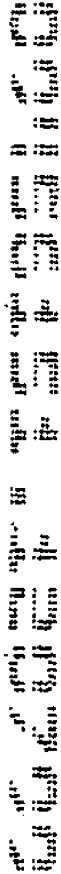
[illegible][illegible]

FIG. 7

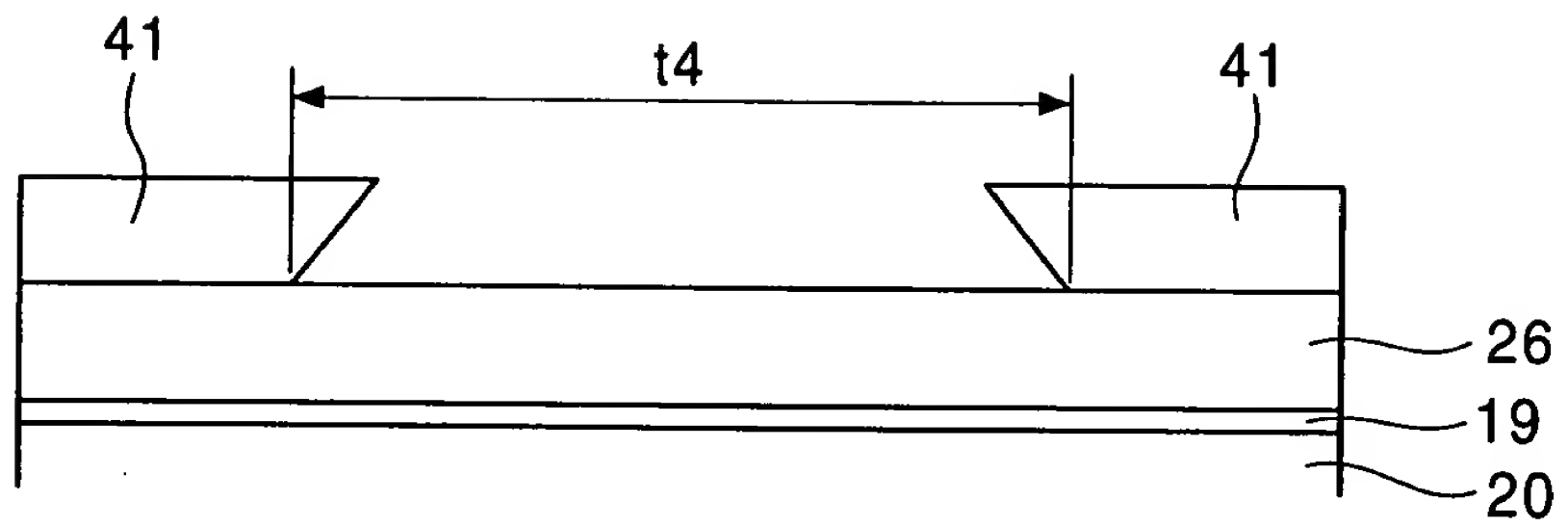


FIG. 8

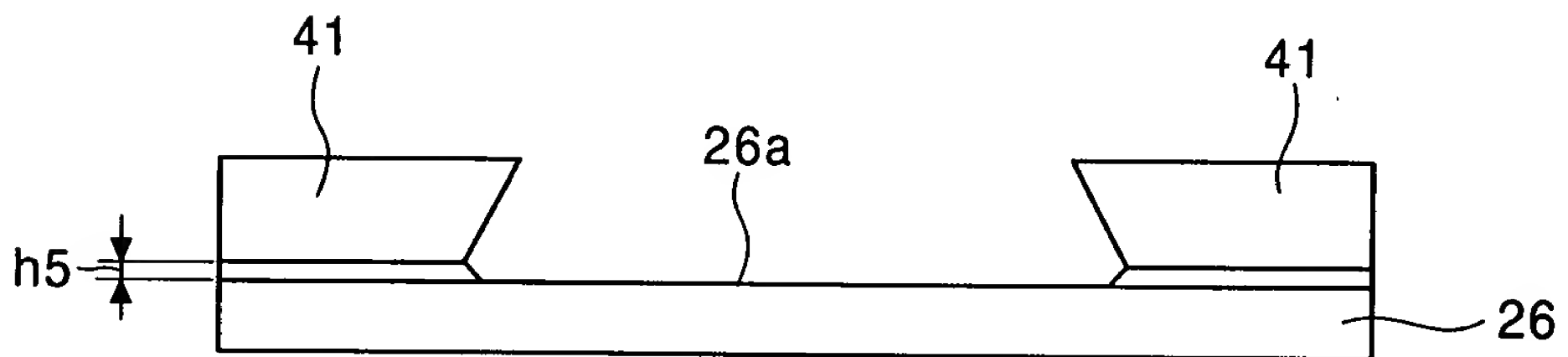


FIG. 9

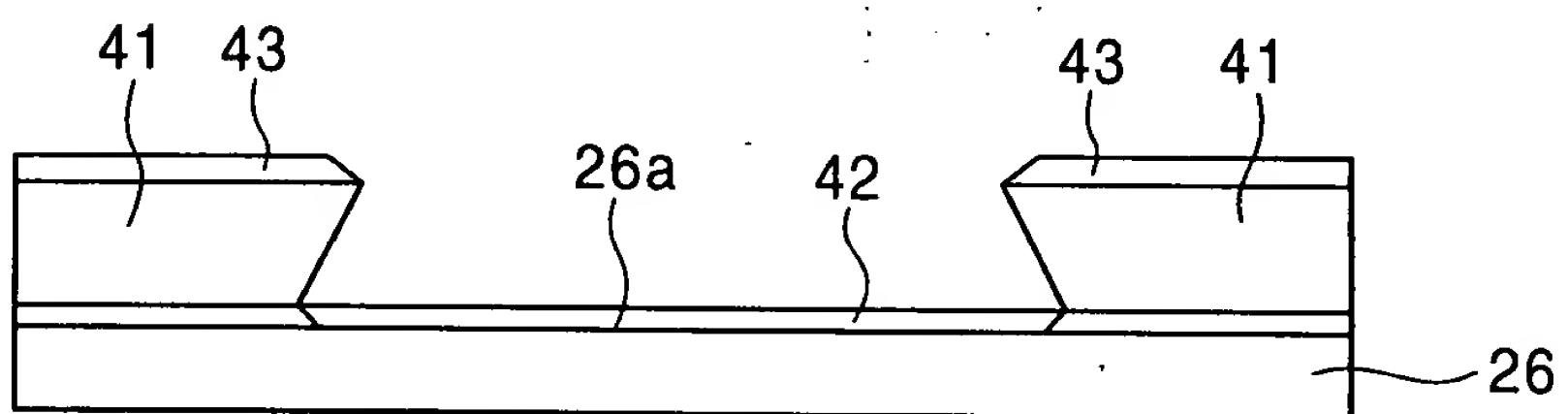


FIG. 10

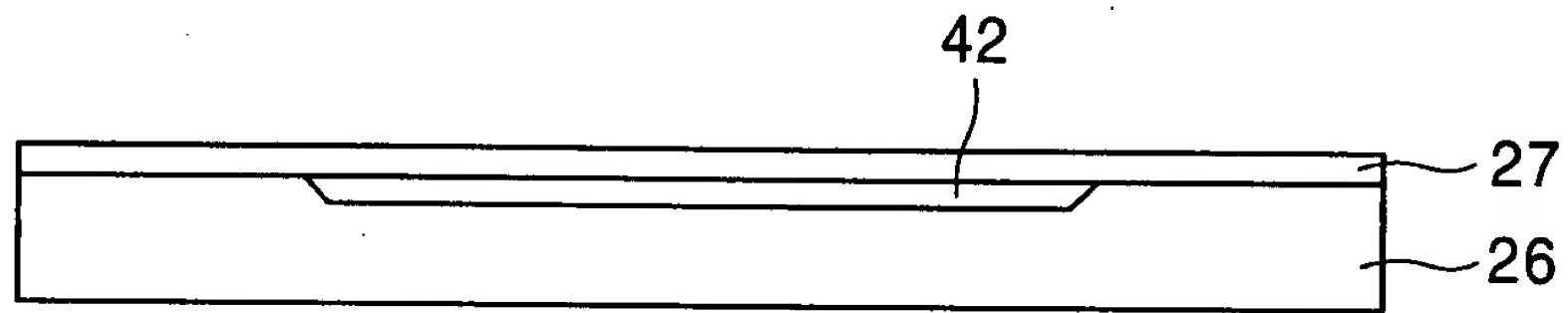


FIG. 11

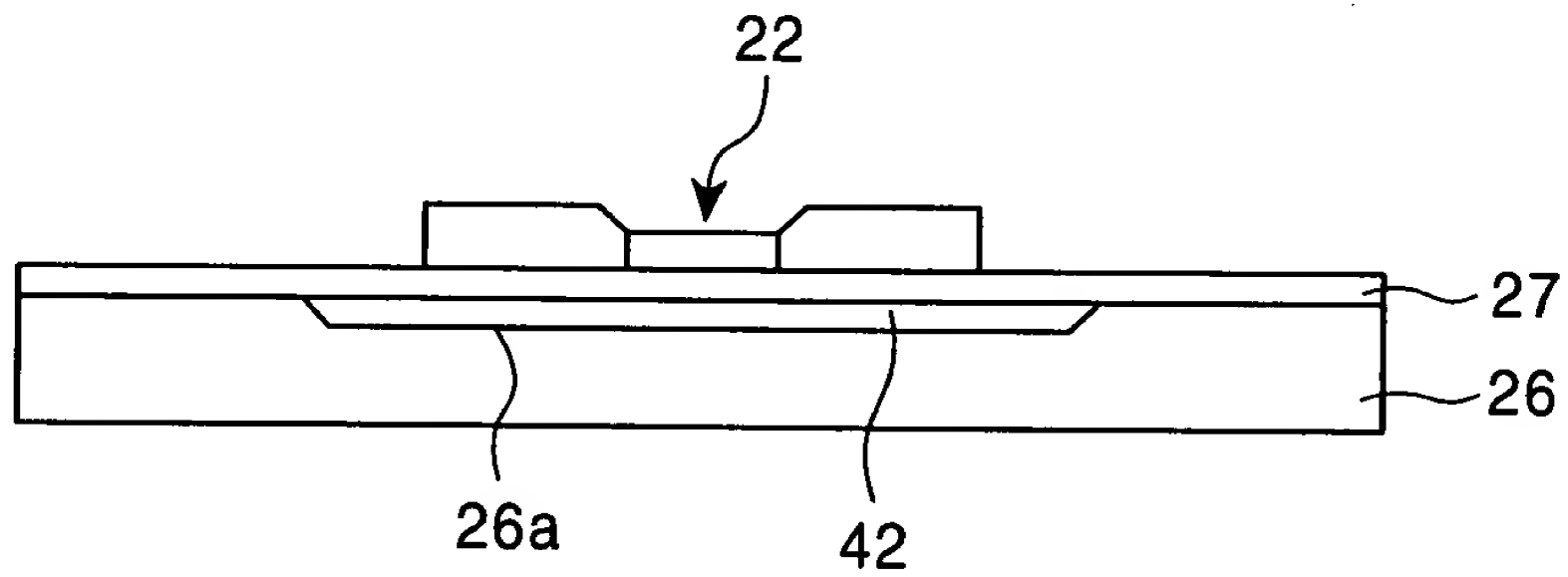


FIG. 12

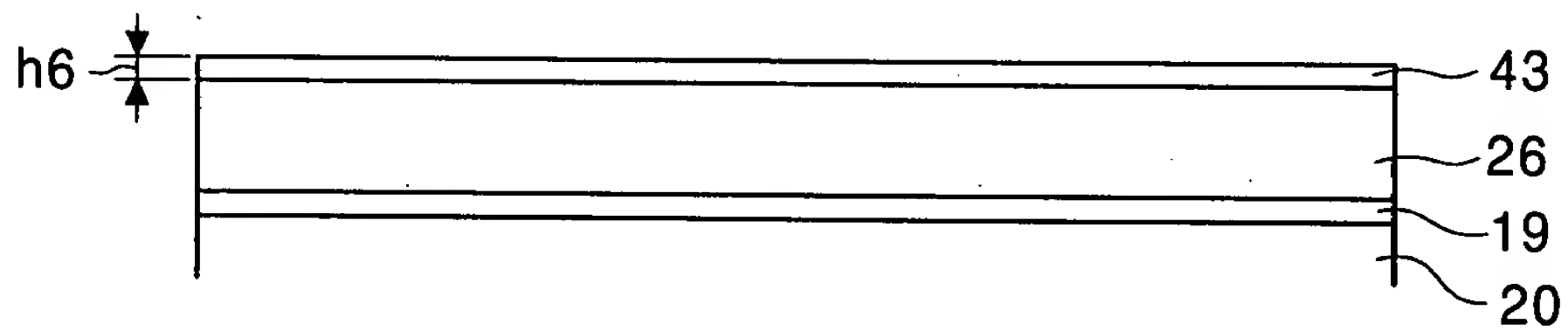


FIG. 13

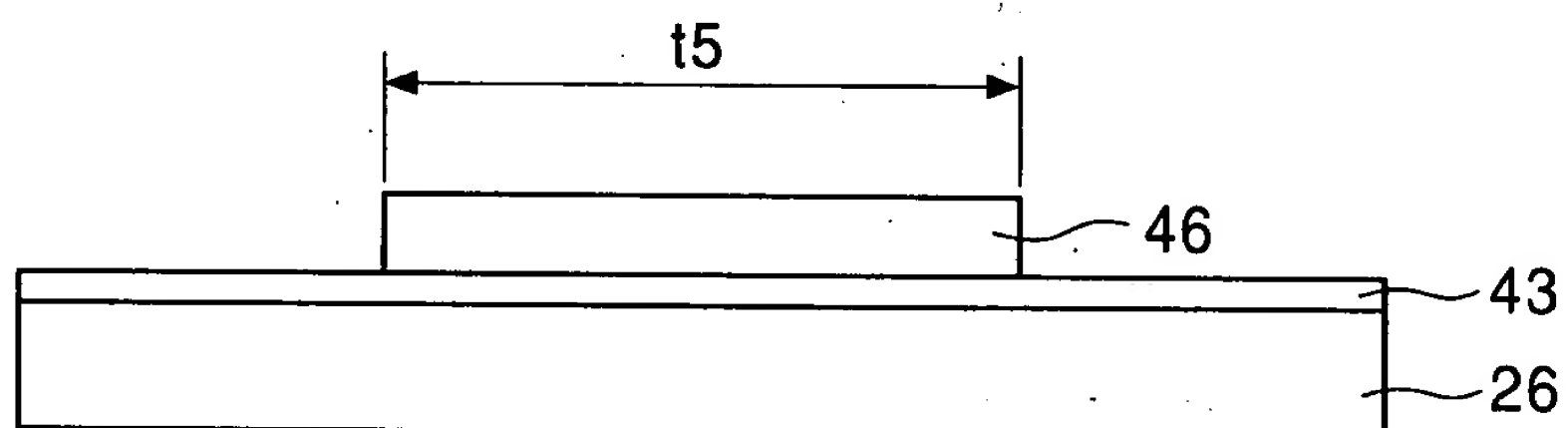


FIG. 14

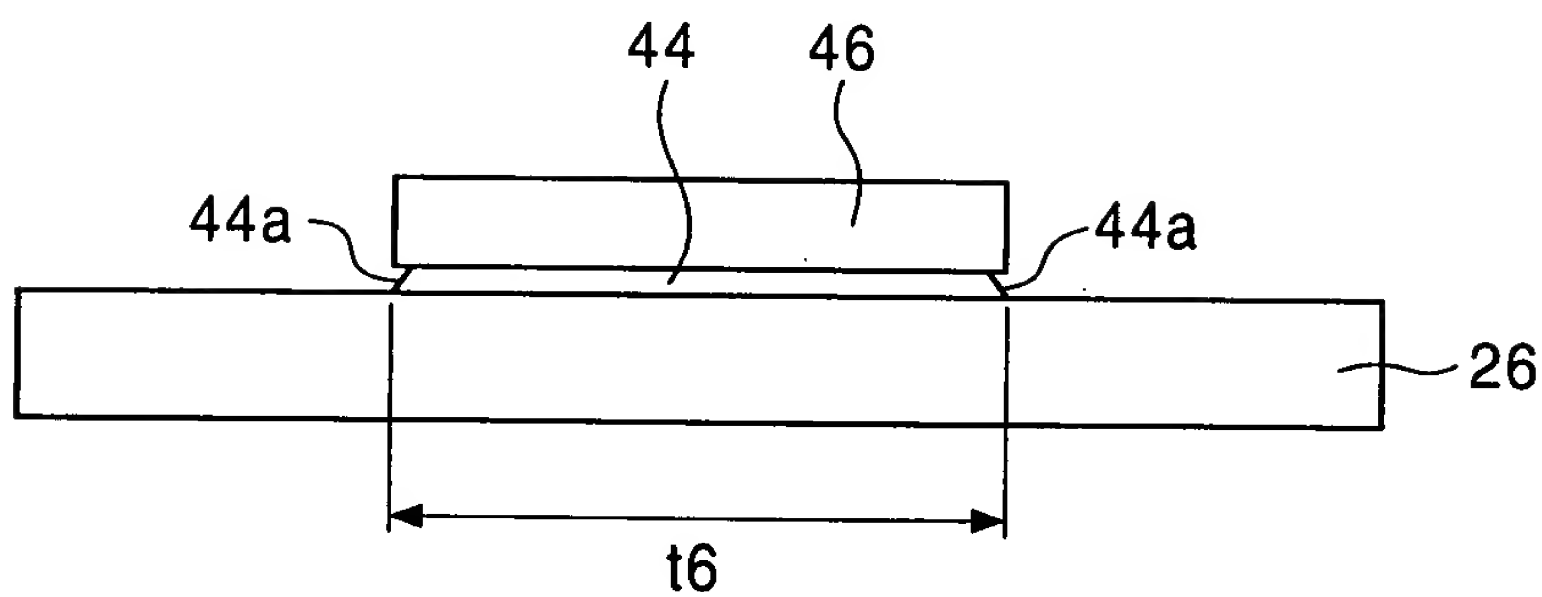


FIG. 15

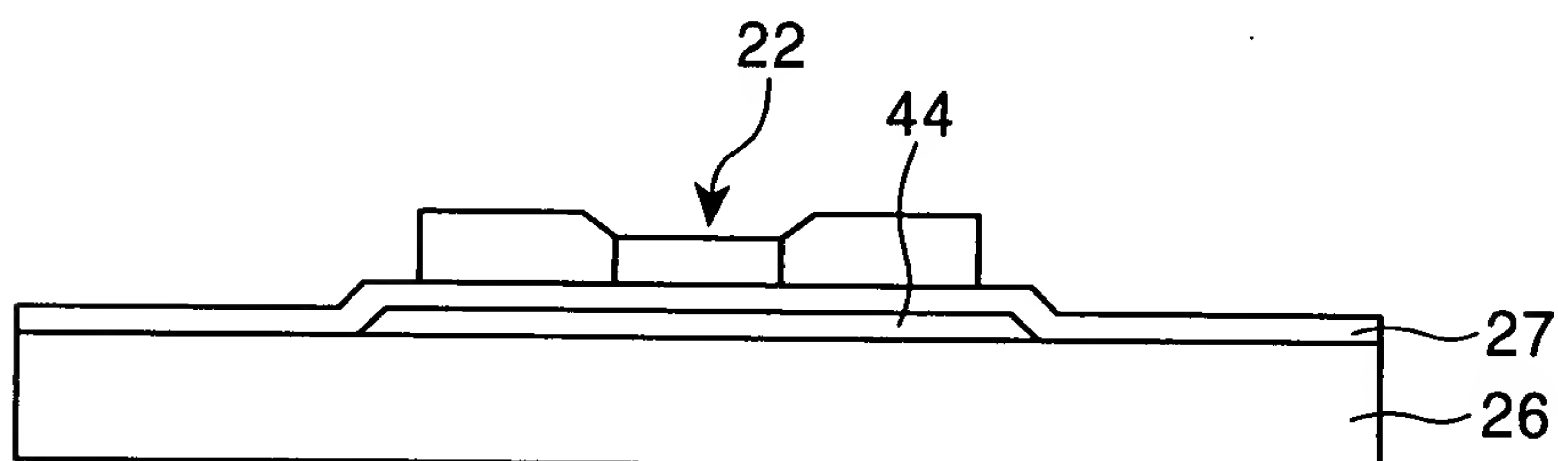


FIG. 16

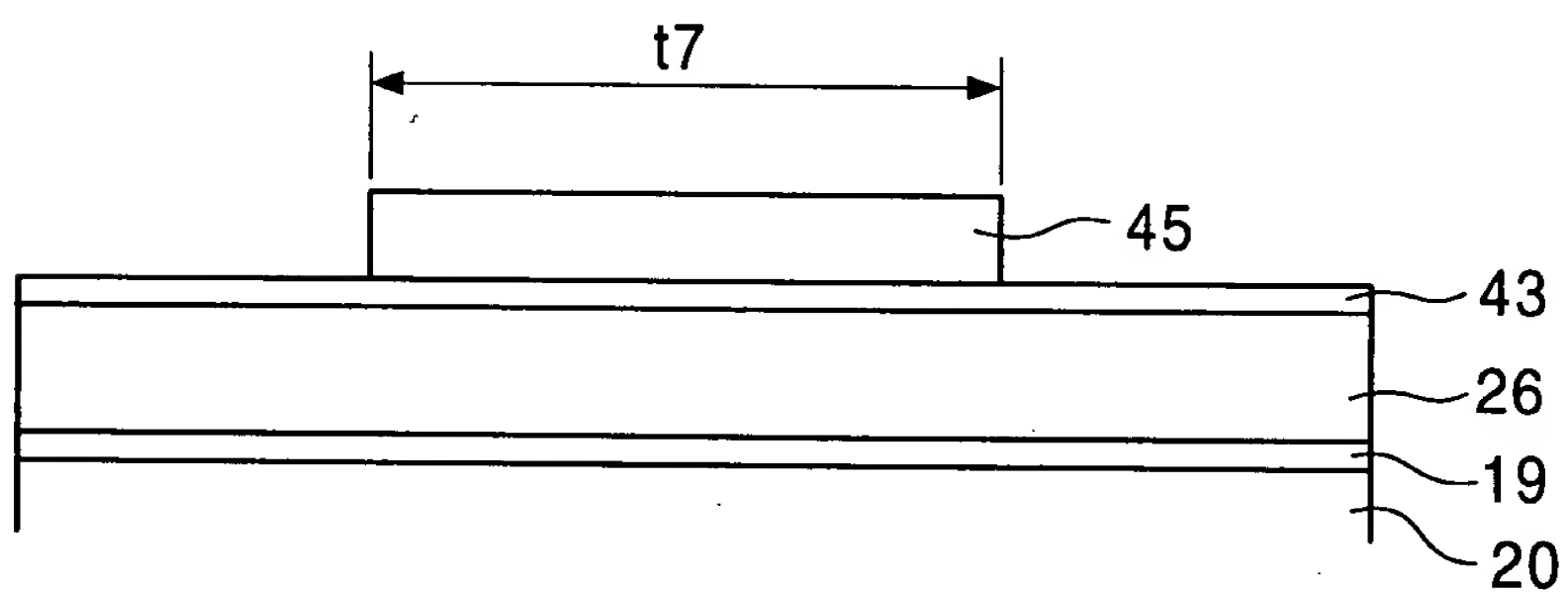


FIG. 17

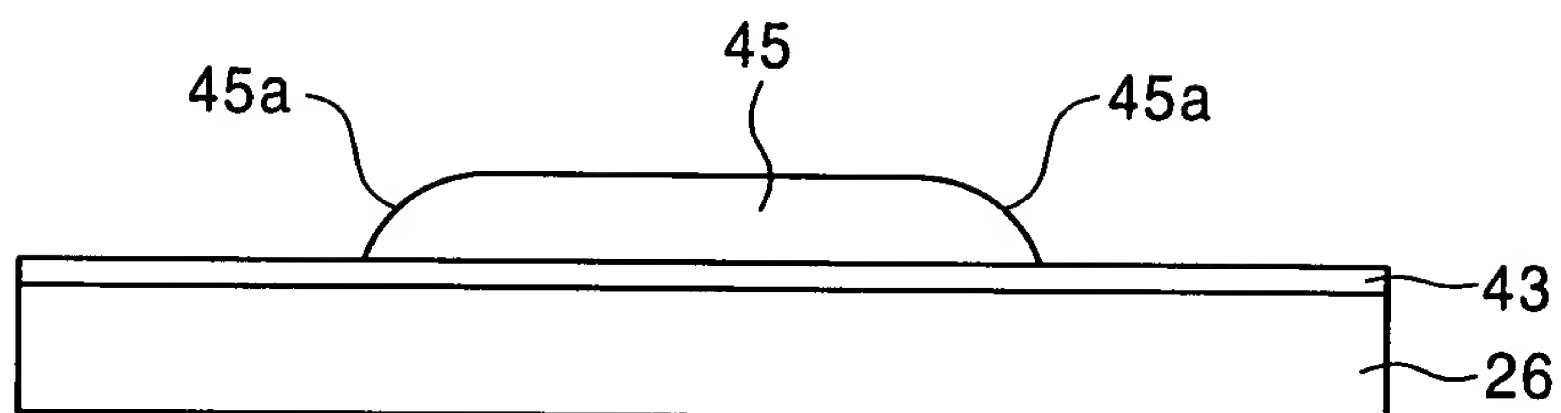


FIG. 18

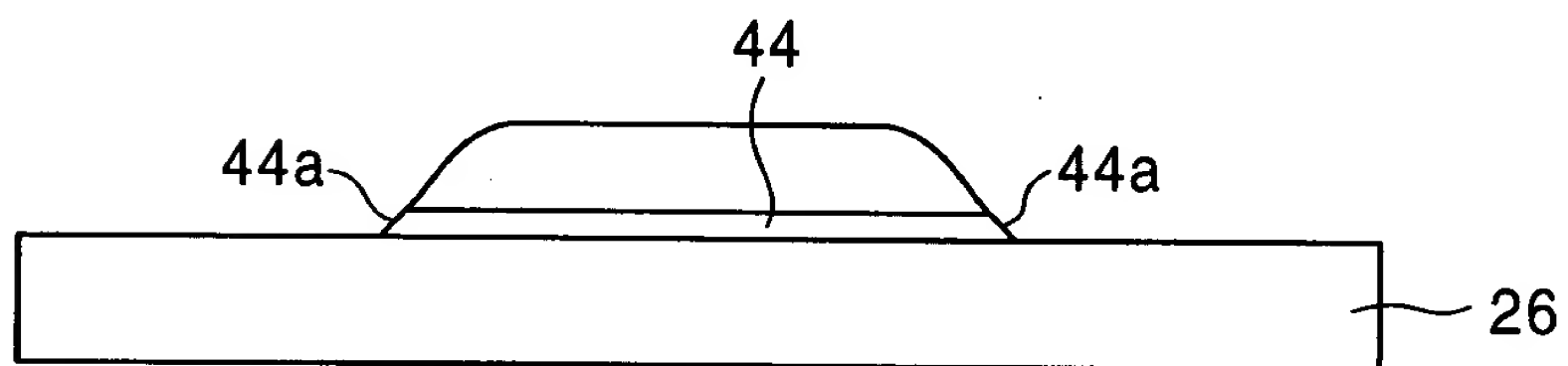


FIG. 19

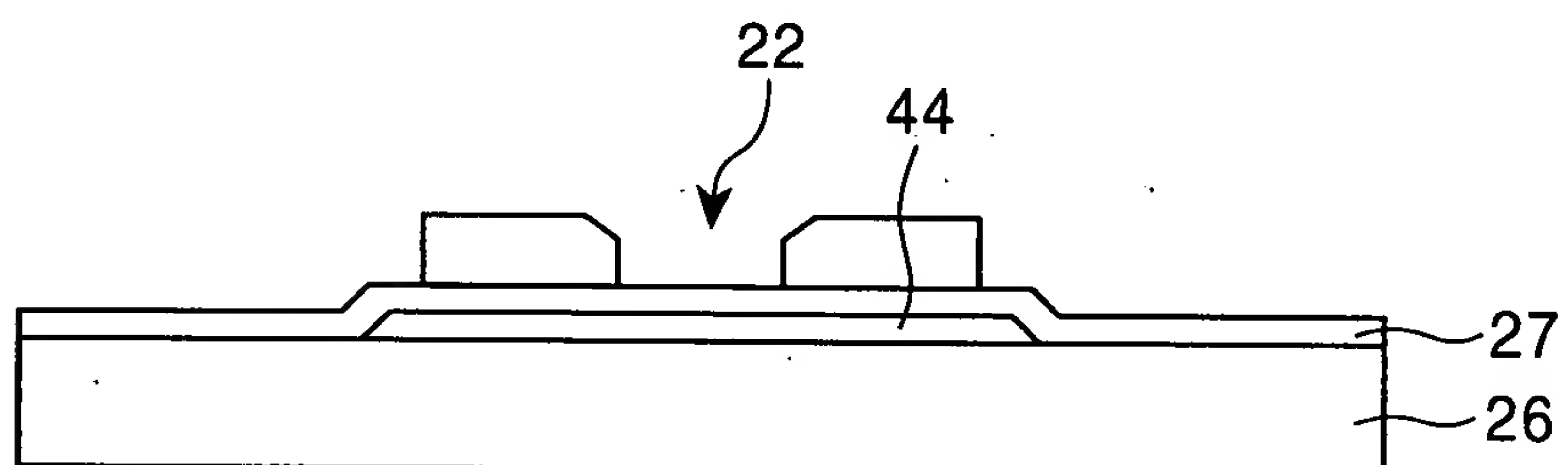


FIG. 20

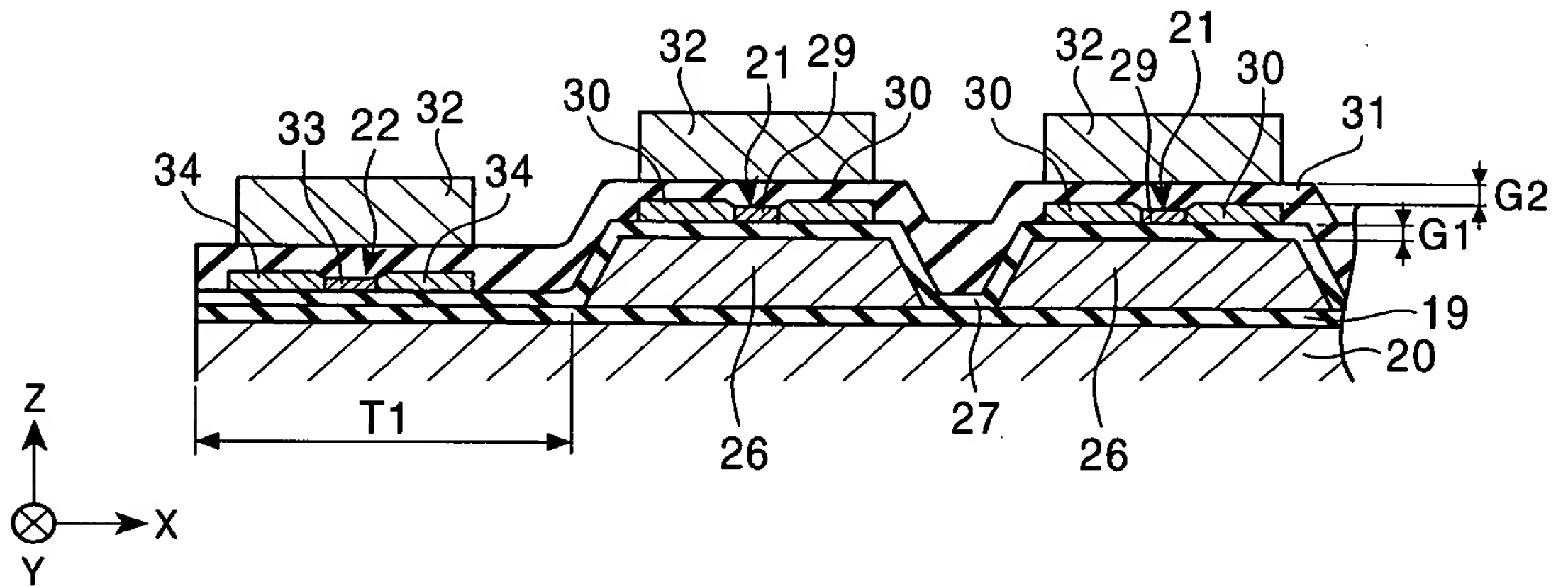


FIG. 21

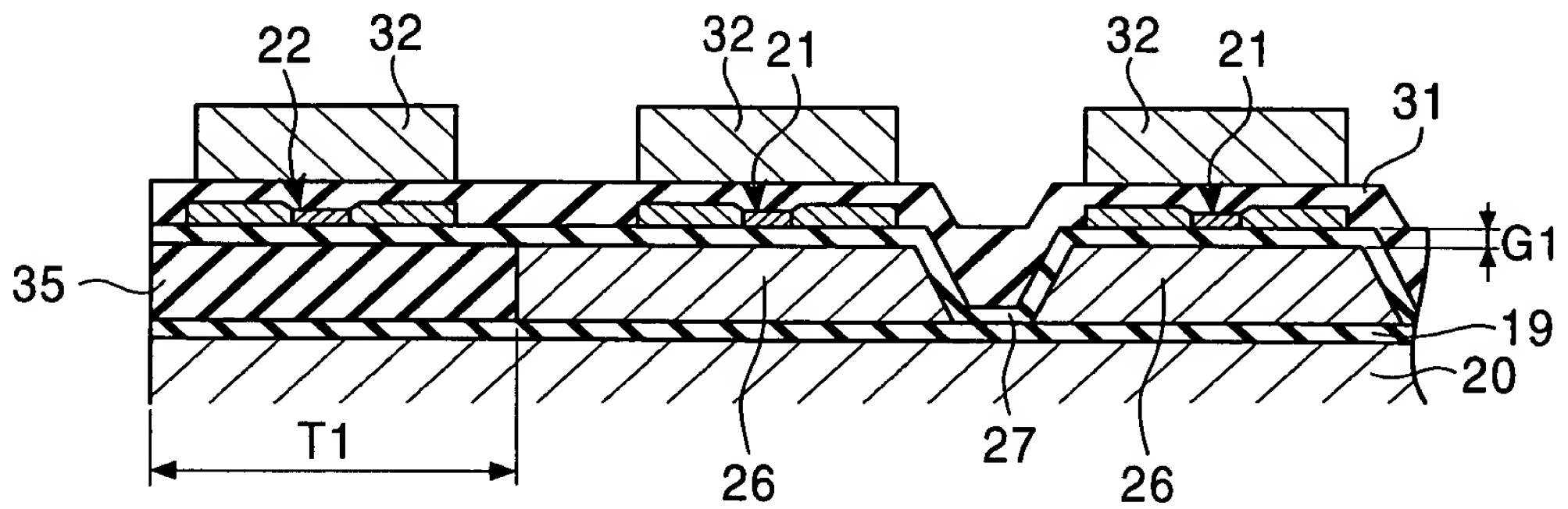


FIG. 22

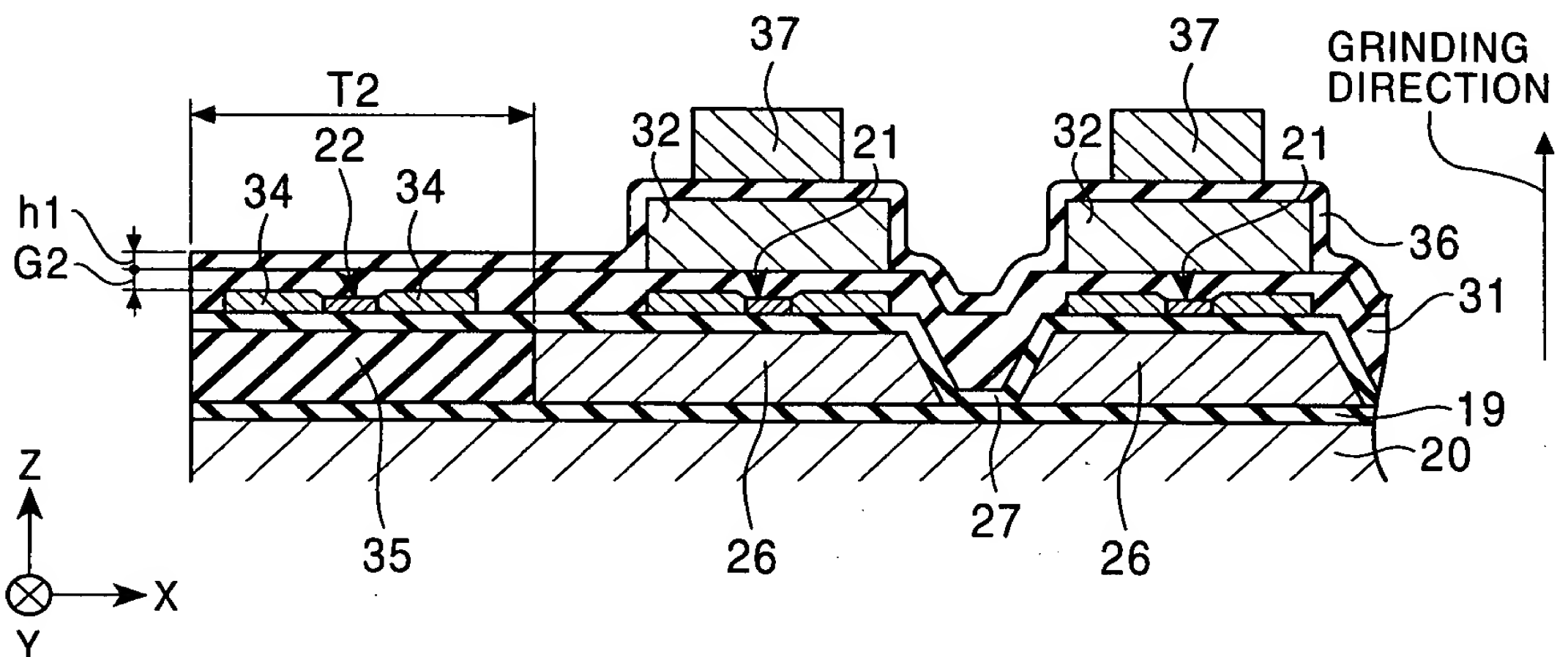




FIG. 23

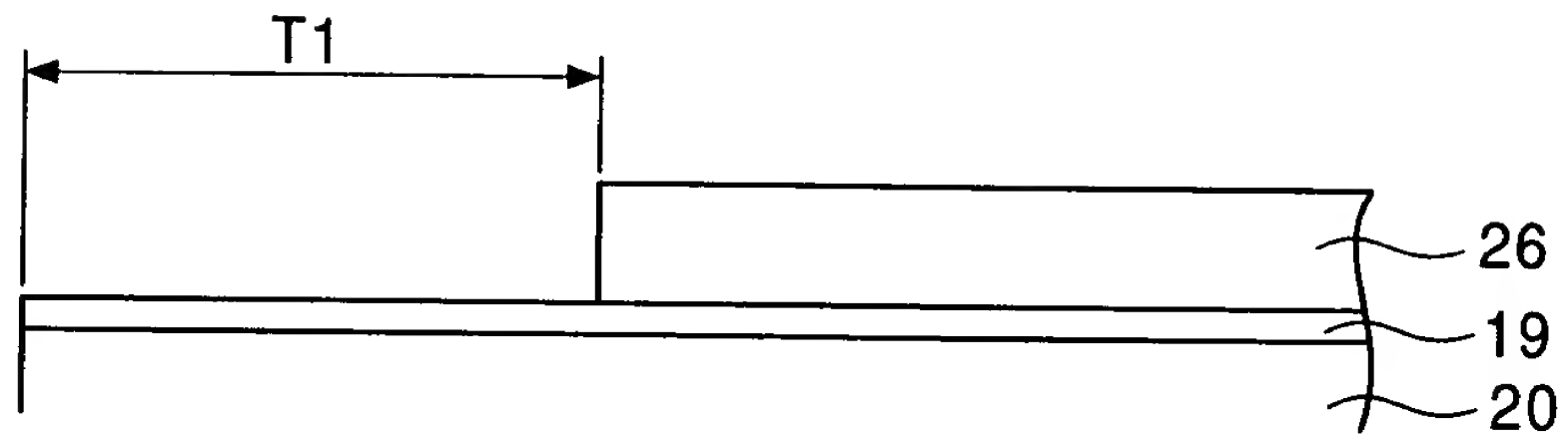


FIG. 24

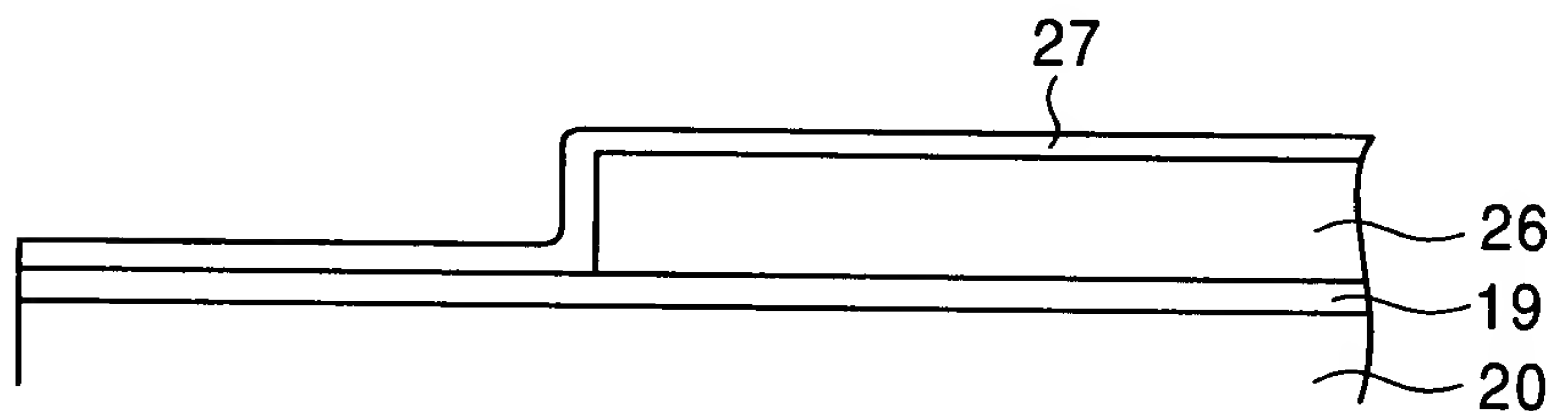


FIG. 25

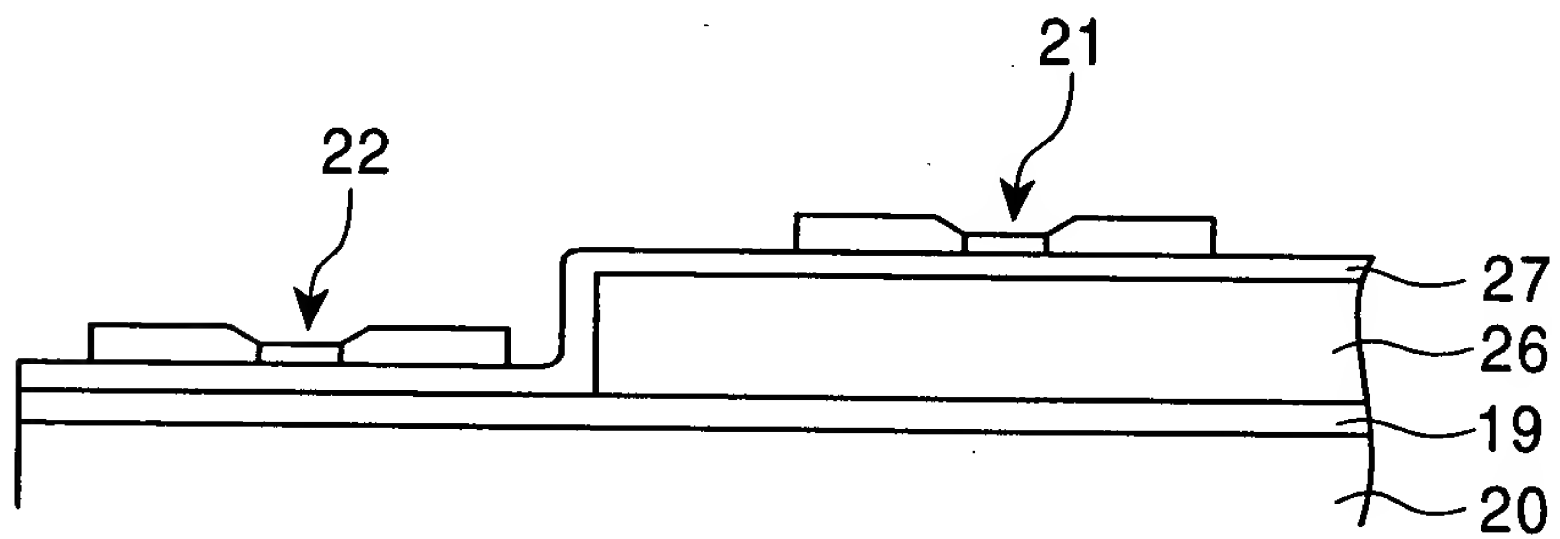


FIG. 26

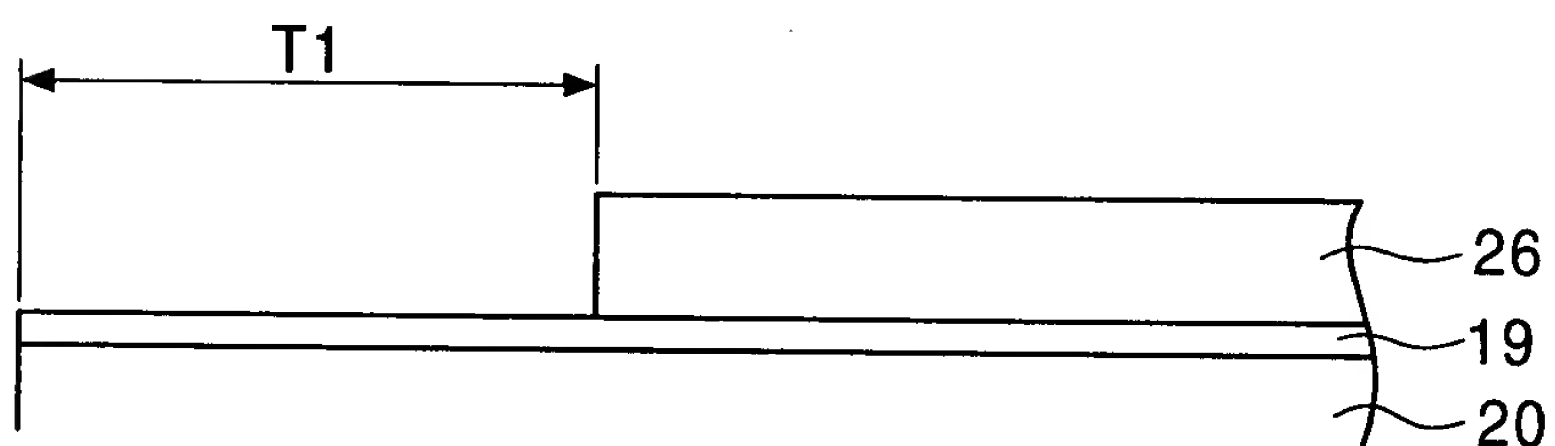


FIG. 27

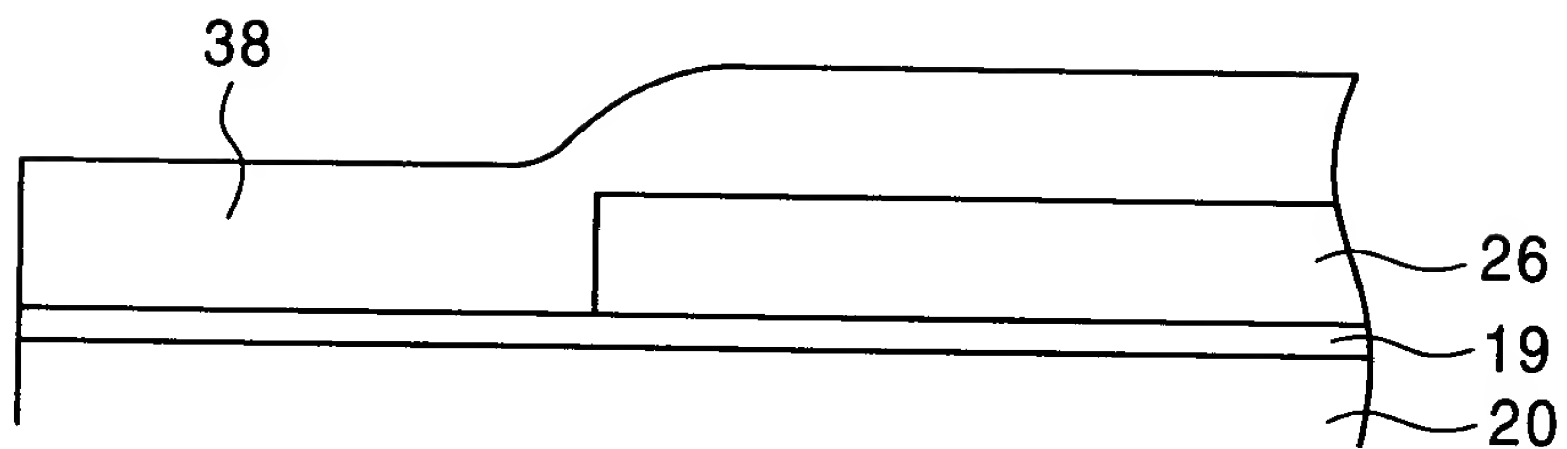


FIG. 28

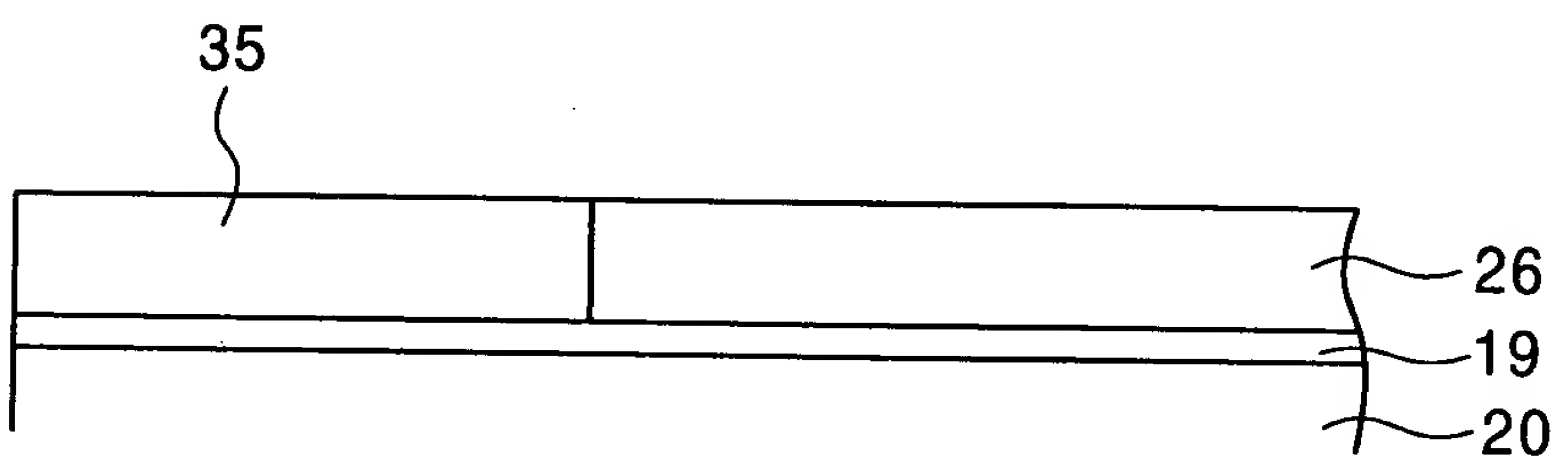


FIG. 29

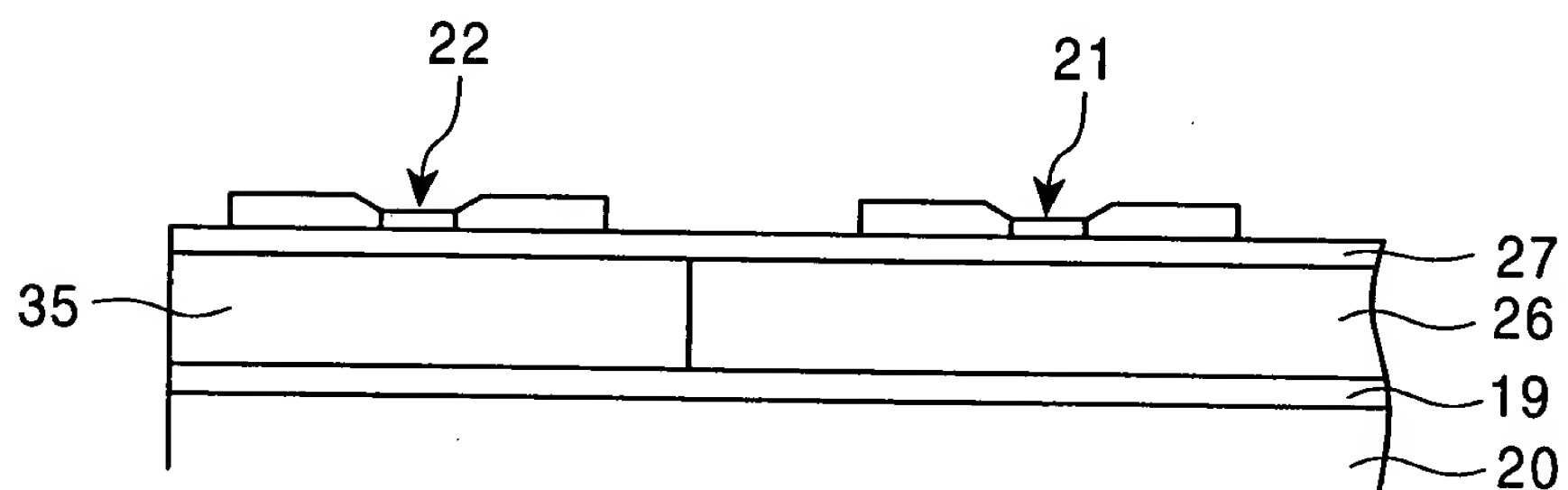


FIG. 30

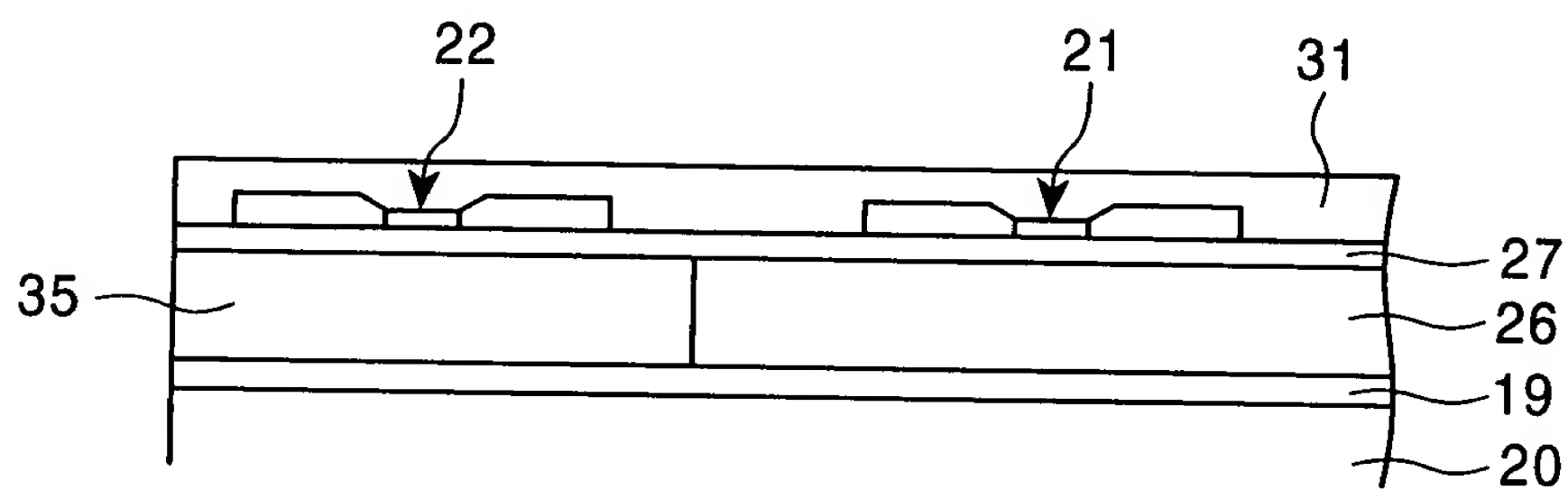


FIG. 31

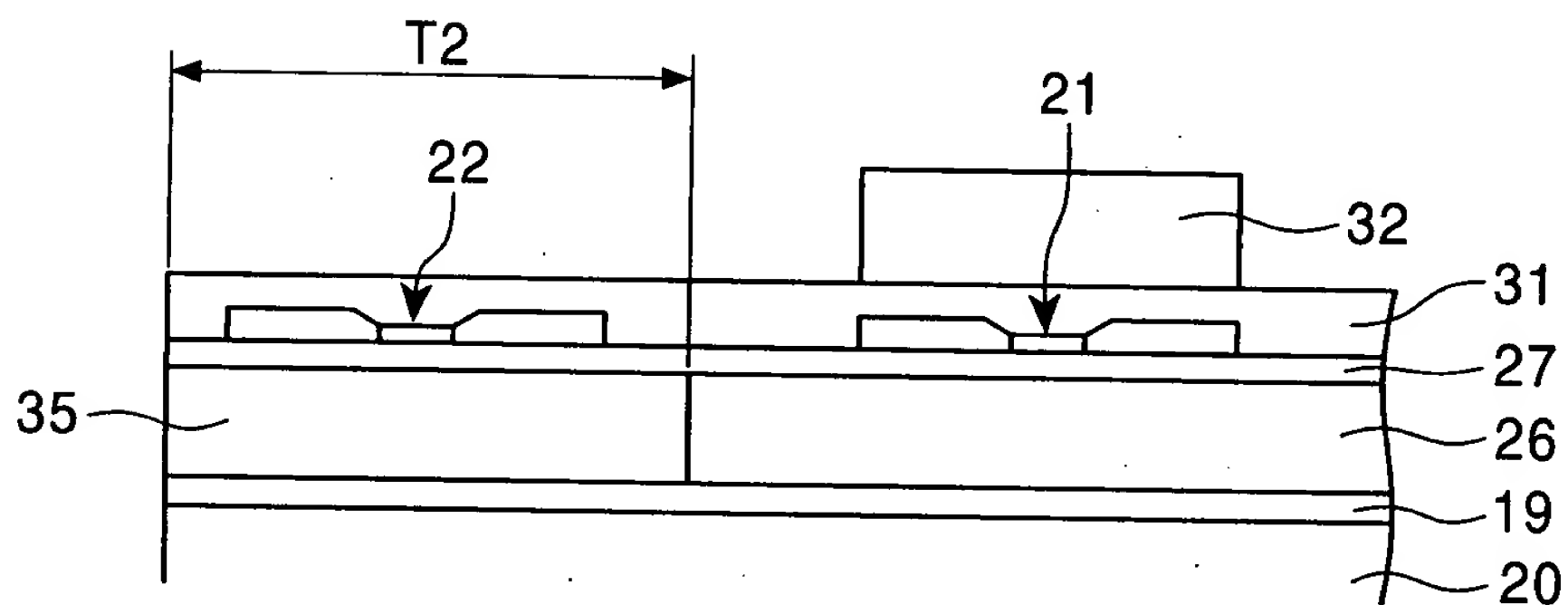


FIG. 32

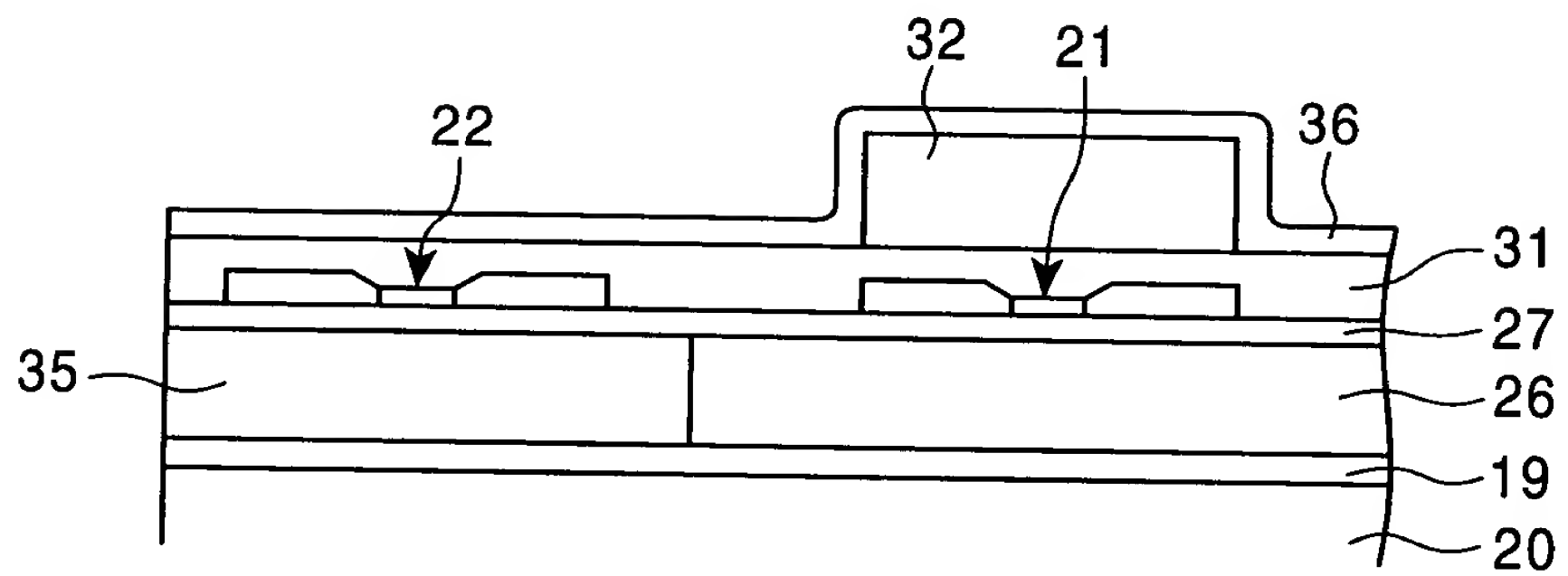
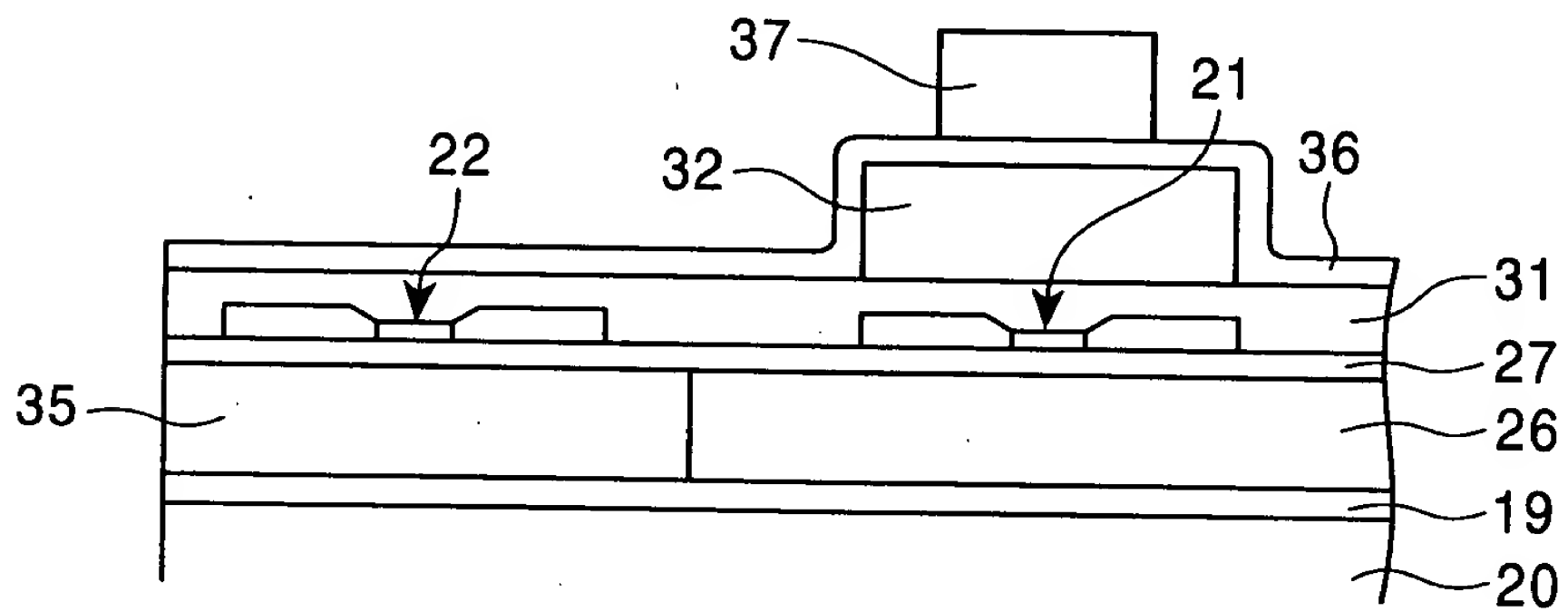
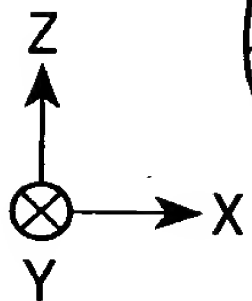


FIG. 33



[illegible]

A detailed cross-sectional diagram of a semiconductor device. It shows three identical unit structures arranged horizontally. Each unit consists of several stacked layers: a top layer 11, a middle layer 9, a thin layer 8, another middle layer 9, and a bottom layer 7. These units are separated by recessed regions containing layers 6 and 4. Below these is a common layer 10, followed by a thick substrate 1. A base layer 3 is located between the units. Various other layers like 12 and 12a are also present. A coordinate system at the bottom left indicates X, Y, and Z axes. Two dimensions, G1 and G2, are marked on the left side.